



Ultrahigh-Speed Switching Applications

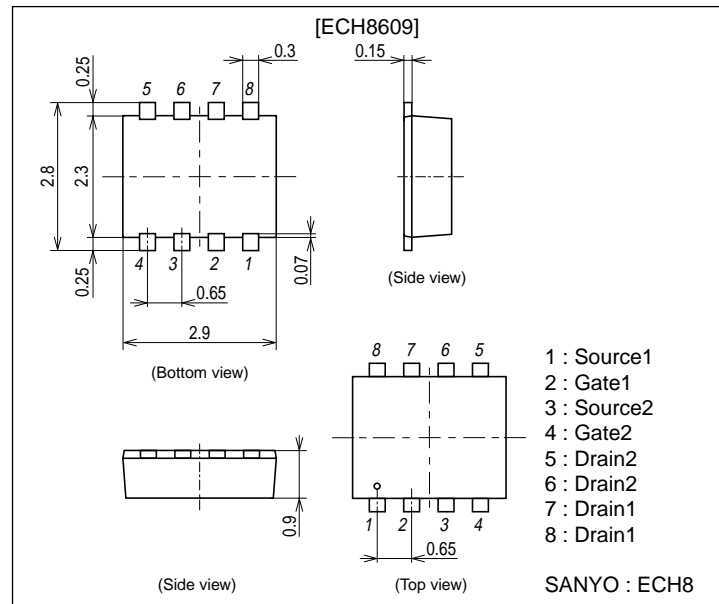
Preliminary

Features

- The ECH8609 incorporates an N-channel MOSFET and a P-channel MOSFET that feature low ON-resistance and high-speed switching, thereby enabling high-density mounting.
- 4V drive.

Package Dimensions

unit : mm
2206



Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	N-channel	P-channel	Unit
Drain-to-Source Voltage	V _{DSS}		30	-30	V
Gate-to-Source Voltage	V _{GSS}		±20	±20	V
Drain Current (DC)	I _D		6	-4	A
Drain Current (Pulse)	I _{DP}	PW≤10μs, duty cycle≤1%	40	-40	A
Allowable Power Dissipation	P _D	Mounted on a ceramic board (900mm²×0.8mm) 1unit	1.3		W
Total Power Dissipation	P _T	Mounted on a ceramic board (900mm²×0.8mm)	1.5		W
Channel Temperature	T _{ch}		150		°C
Storage Temperature	T _{stg}		-55 to +150		°C

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
[N-channel]						
Drain-to-Source Breakdown Voltage	V _{(BR)DSS}	I _D =1mA, V _{GS} =0	30			V
Zero-Gate Voltage Drain Current	I _{DSS}	V _{DS} =30V, V _{GS} =0			1	μA
Gate-to-Source Leakage Current	I _{GSS}	V _{GS} =±16V, V _{DS} =0			±10	μA

Marking : FB

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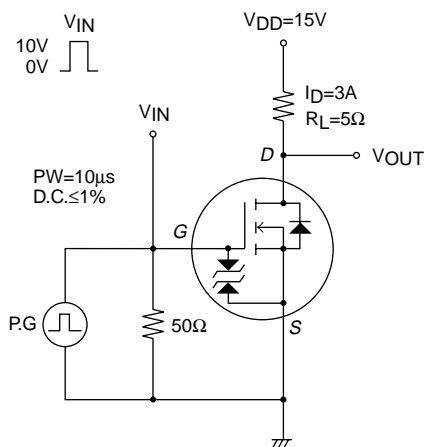
ECH8609

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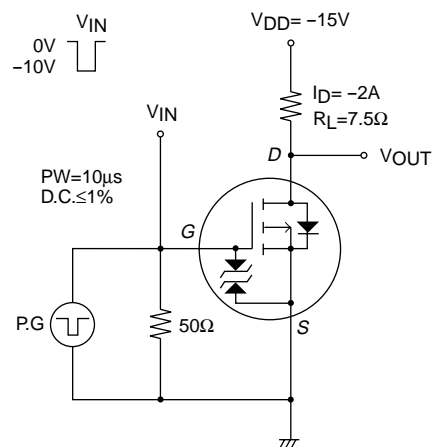
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Cutoff Voltage	$V_{GS(off)}$	$V_{DS}=10V, I_D=1mA$	1.0		2.4	V
Forward Transfer Admittance	$ y_{fs} $	$V_{DS}=10V, I_D=3A$	3.3	5		S
Static Drain-to-Source On-State Resistance	$R_{DS(on)1}$	$I_D=2A, V_{GS}=10V$		25	34	$m\Omega$
	$R_{DS(on)2}$	$I_D=1A, V_{GS}=4V$		52	75	$m\Omega$
Input Capacitance	C_{iss}	$V_{DS}=10V, f=1MHz$		510		pF
Output Capacitance	C_{oss}	$V_{DS}=10V, f=1MHz$		105		pF
Reverse Transfer Capacitance	C_{rss}	$V_{DS}=10V, f=1MHz$		70		pF
Turn-ON Delay Time	$t_d(on)$	See specified Test Circuit.		15		ns
Rise Time	t_r	See specified Test Circuit.		74		ns
Turn-OFF Delay Time	$t_d(off)$	See specified Test Circuit.		43		ns
Fall Time	t_f	See specified Test Circuit.		37		ns
Total Gate Charge	Q_g	$V_{DS}=10V, V_{GS}=10V, I_D=6A$		11		nC
Gate-to-Source Charge	Q_{gs}	$V_{DS}=10V, V_{GS}=10V, I_D=6A$		1.9		nC
Gate-to-Drain "Miller" Charge	Q_{gd}	$V_{DS}=10V, V_{GS}=10V, I_D=6A$		2.9		nC
Diode Forward Voltage	V_{SD}	$I_S=6A, V_{GS}=0$		0.85	1.2	V
[P-channel]						
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$I_D=-1mA, V_{GS}=0$	-30			V
Zero-Gate Voltage Drain Current	I_{DSS}	$V_{DS}=-30V, V_{GS}=0$			-1	μA
Gate-to-Source Leakage Current	I_{GSS}	$V_{GS}=\pm 16V, V_{DS}=0$			± 10	μA
Cutoff Voltage	$V_{GS(off)}$	$V_{DS}=-10V, I_D=-1mA$	-1.0		-2.4	V
Forward Transfer Admittance	$ y_{fs} $	$V_{DS}=-10V, I_D=-2A$	3.3	5		S
Static Drain-to-Source On-State Resistance	$R_{DS(on)1}$	$I_D=-2A, V_{GS}=-10V$		50	67	$m\Omega$
	$R_{DS(on)2}$	$I_D=-1A, V_{GS}=-4V$		87	120	$m\Omega$
Input Capacitance	C_{iss}	$V_{DS}=-10V, f=1MHz$		550		pF
Output Capacitance	C_{oss}	$V_{DS}=-10V, f=1MHz$		120		pF
Reverse Transfer Capacitance	C_{rss}	$V_{DS}=-10V, f=1MHz$		90		pF
Turn-ON Delay Time	$t_d(on)$	See specified Test Circuit.		13		ns
Rise Time	t_r	See specified Test Circuit.		110		ns
Turn-OFF Delay Time	$t_d(off)$	See specified Test Circuit.		65		ns
Fall Time	t_f	See specified Test Circuit.		75		ns
Total Gate Charge	Q_g	$V_{DS}=-10V, V_{GS}=-10V, I_D=-4A$		14		nC
Gate-to-Source Charge	Q_{gs}	$V_{DS}=-10V, V_{GS}=-10V, I_D=-4A$		2.2		nC
Gate-to-Drain "Miller" Charge	Q_{gd}	$V_{DS}=-10V, V_{GS}=-10V, I_D=-4A$		2.5		nC
Diode Forward Voltage	V_{SD}	$I_S=-4A, V_{GS}=0$		-0.88	-1.2	V

Switching Time Test Circuit

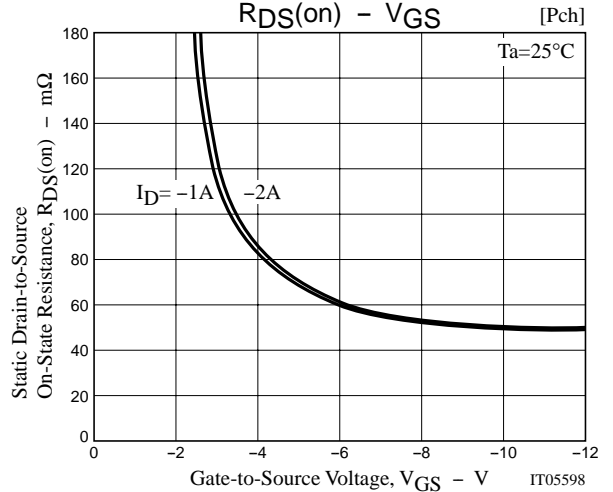
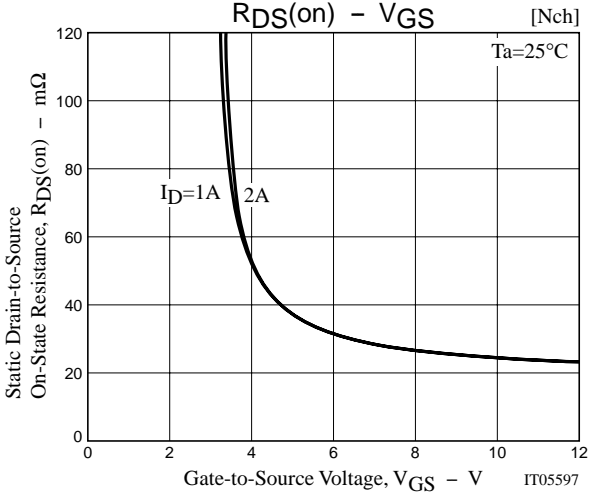
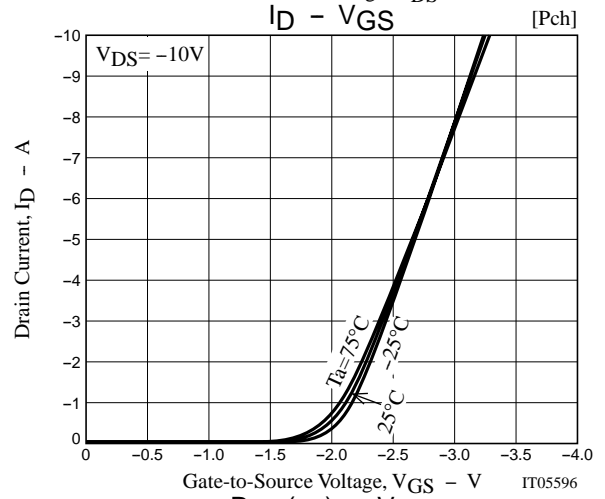
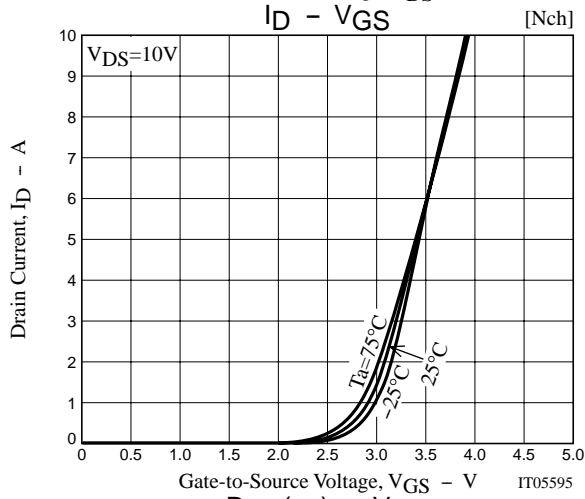
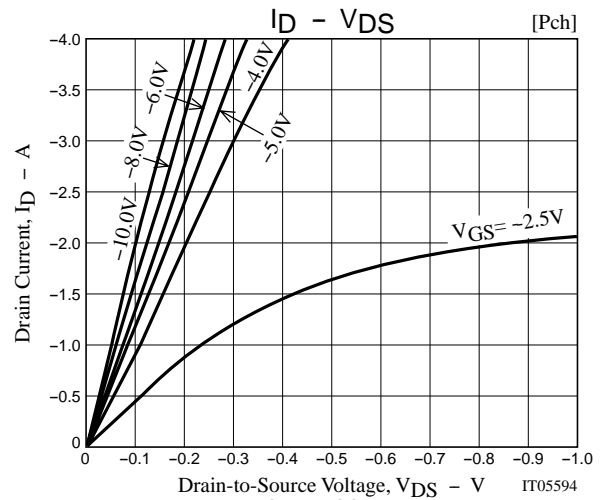
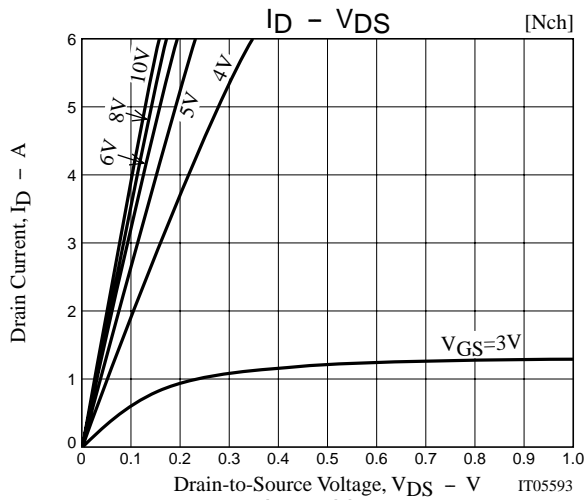
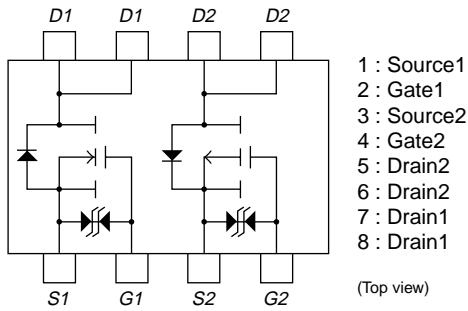
[N-channel]



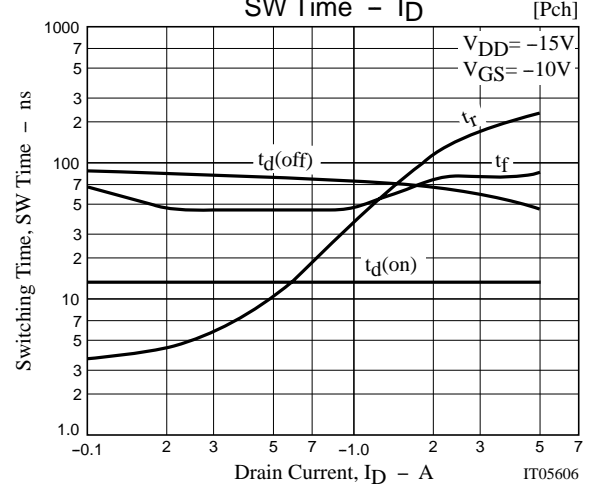
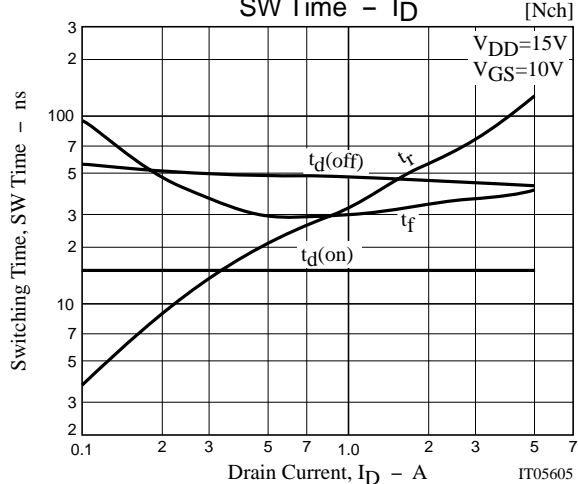
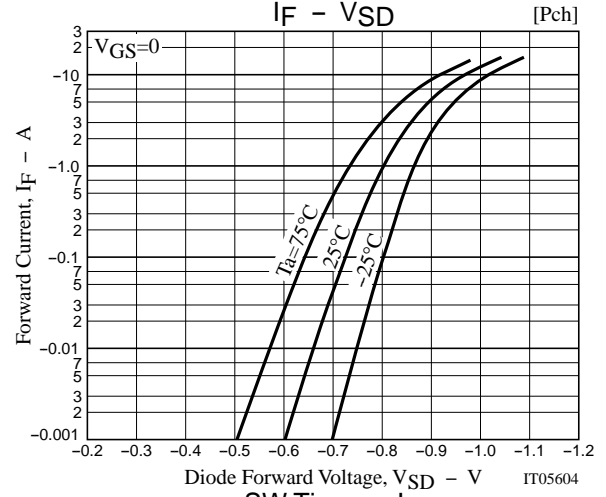
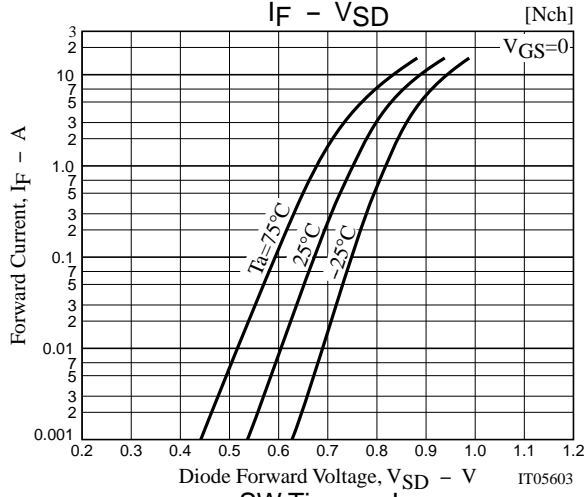
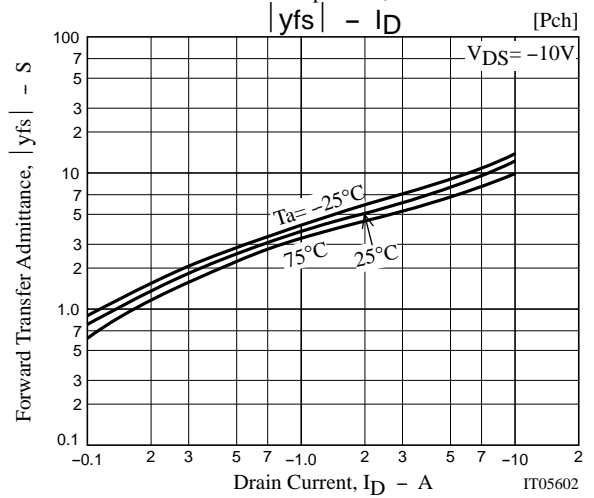
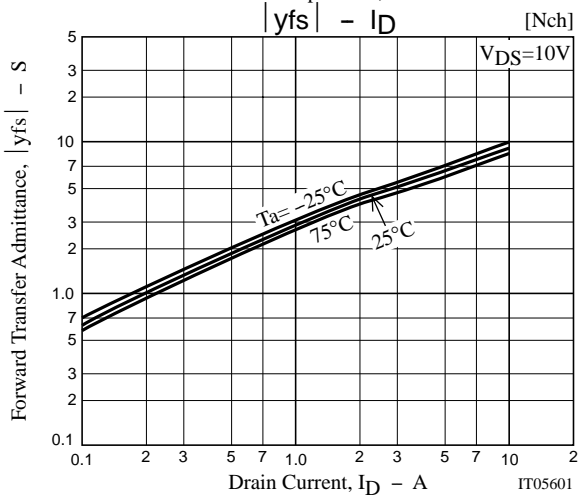
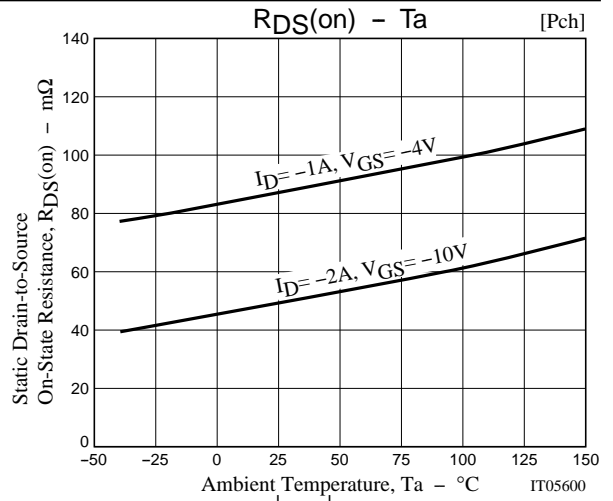
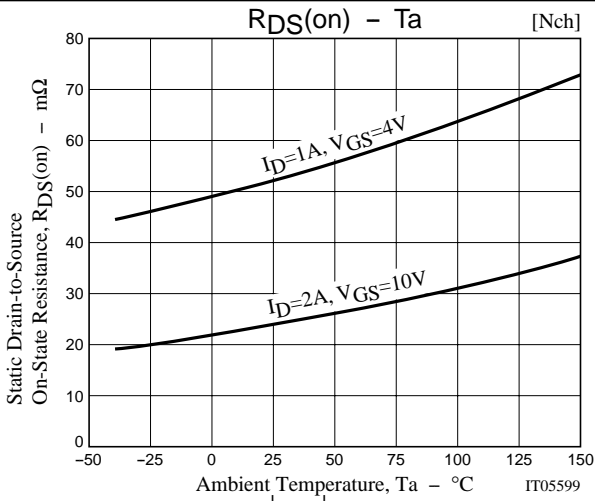
[P-channel]

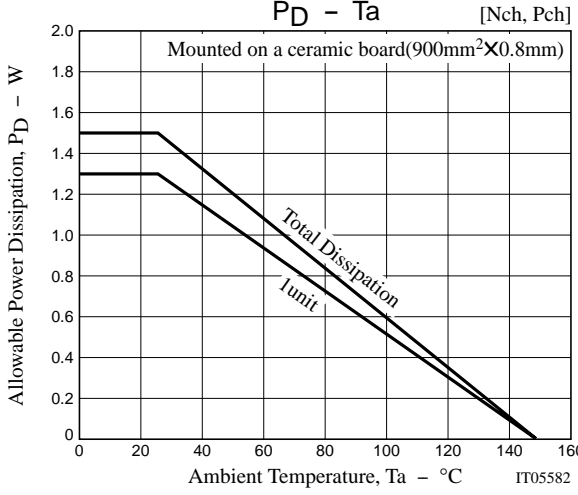
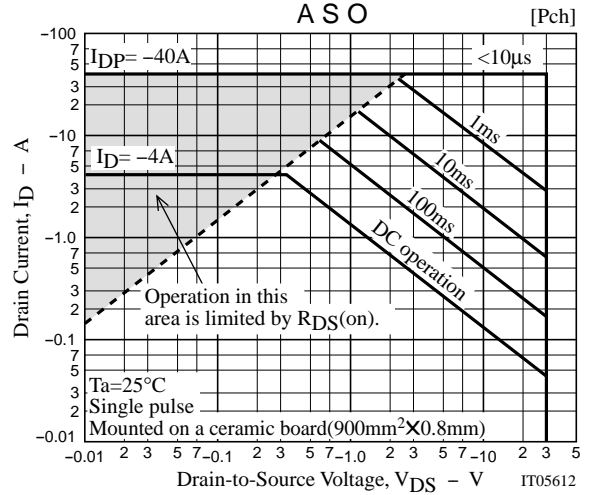
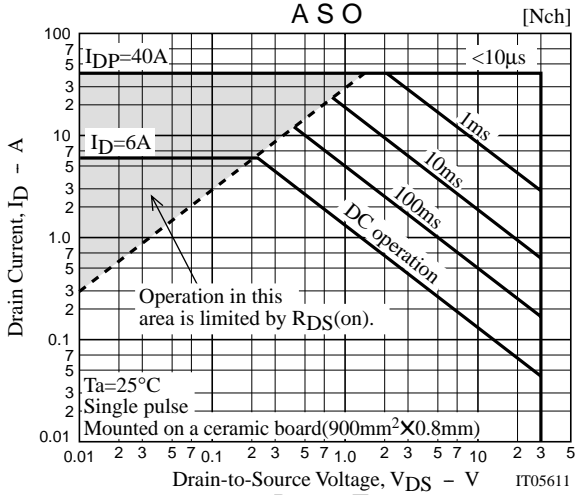
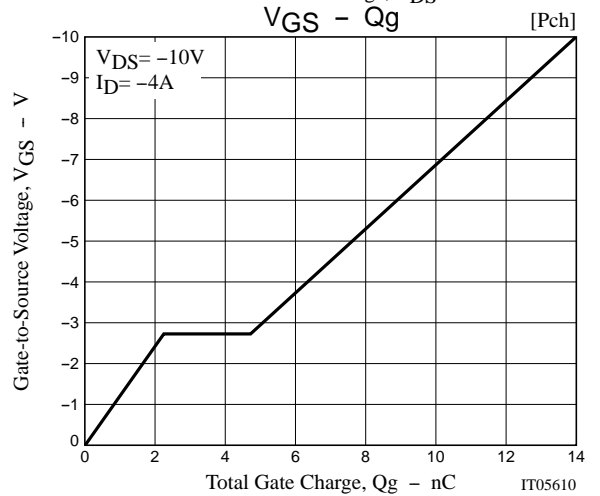
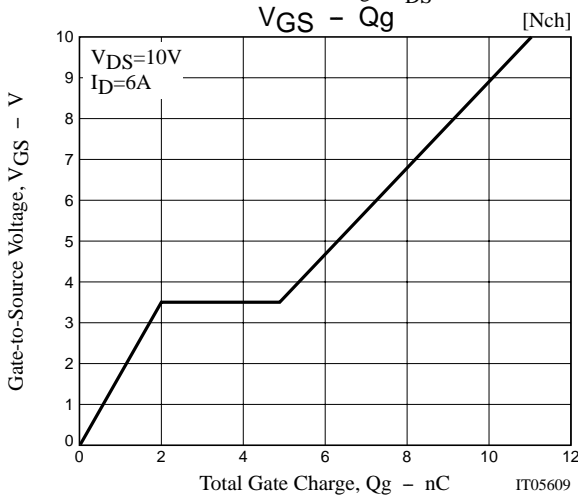
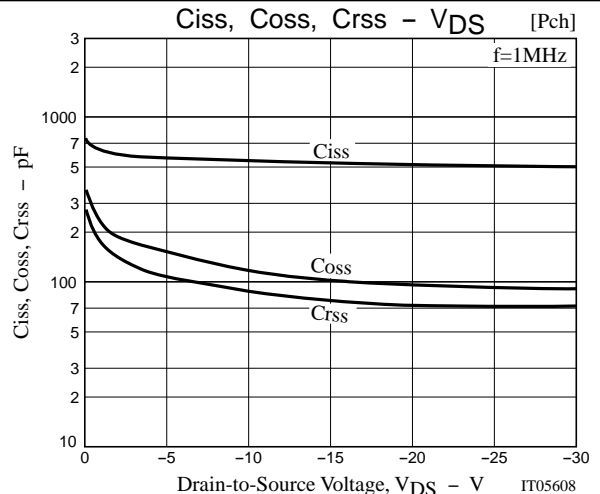
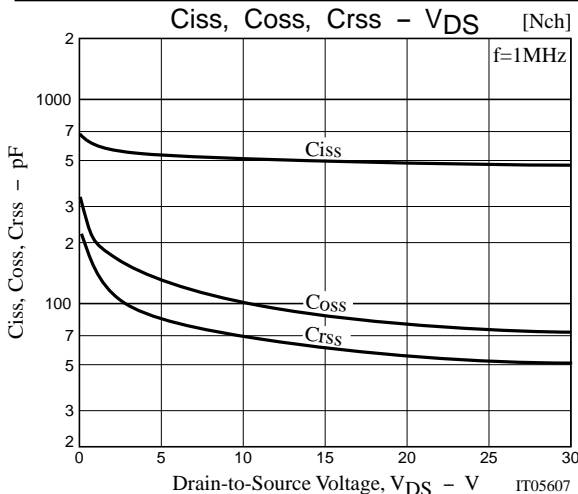


Electrical Connection



ECH8609





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